

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) An electrostatic attraction mechanism, comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block and
a first of the pair of attraction terminals is larger in size than a second of the pair of
attraction terminals, and

a power source for applying a voltage to each of the attraction terminals to
electrostatically attract a plate-shaped object to the dielectric block by inducing static
electricity on the attraction surface,

wherein the voltage applied to each of the terminals can be individually
adjusted in order to control a surface potential of the plate shaped object.

2. (Original) The electrostatic attraction mechanism of claim 1, wherein a
plurality of pairs of attraction terminals are mounted inside the dielectric block.

3. (Original) The electrostatic attraction mechanism of claim 2, wherein the voltage applied to each of the plurality of pairs of terminals can be individually adjusted in order to control the surface potential of the plate shaped object.

4. (Currently Amended) An electrostatic attraction mechanism, comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block,

wherein a first of the pair of attraction terminals is larger in size than a second of the pair of attraction terminals,

means for applying a voltage to each of the attraction terminals to electrostatically attract a plate-shaped object to the dielectric block by inducing static electricity on the attraction surface, and

means for individually adjusting the voltage applied to each of the terminals in order to control a surface potential of the plate shaped object.

5. (Original) The electrostatic attraction mechanism of claim 4, wherein a plurality of pairs of attraction terminals are mounted inside the dielectric block.

6. (Original) The electrostatic attraction mechanism of claim 5, wherein the voltage applied to each of the plurality of pairs of terminals can be individually adjusted in order to control the surface potential of the plate shaped object.

7. (Original) A surface processing method, comprising the steps of:

holding a plate-shaped object in a prescribed position inside a processing chamber on an attraction surface of a dielectric block, the dielectric block having a pair of attraction terminals mounted inside the dielectric block,

electrostatically attracting the plate-shaped object to the dielectric block by applying a voltage to the pair of attraction terminals to induce static electricity on the attraction surface,

independently controlling the voltages applied to each of the respective attraction terminals constituting said pair of attraction terminals to adjust a surface potential of the plate-shaped object in order to suppress injection of charged particles into the plate-shaped object, and

processing is carried out while the plate-shaped object is attracted to the dielectric block.

8. (Currently Amended) The method of claim 7, A surface processing method, comprising the steps of:

holding a plate-shaped object in a prescribed position inside a processing chamber on an attraction surface of a dielectric block, the dielectric block having a pair of attraction terminals mounted inside the dielectric block,

electrostatically attracting the plate-shaped object to the dielectric block by applying a voltage to the pair of attraction terminals to induce static electricity on the attraction surface,

independently controlling the voltages applied to each of the respective attraction terminals constituting said pair of attraction terminals to adjust a surface potential of the plate-shaped object in order to suppress injection of charged particles into the plate-shaped object, and

processing is carried out while the plate-shaped object is attracted to the dielectric block,

wherein the controlling step is carried out while determining a relationship between the applied voltages and the surface potential by measuring in advance the surface potential of the plate-shaped object while respectively changing the voltages applied to the attraction terminals, and controlling the voltages applied to the attraction terminals in accordance with this relationship.

Claims 9-12 (Canceled).

13. (Previously Presented) The electrostatic attraction mechanism of claim 1, wherein the pair of attraction terminals are arranged inside the dielectric block in a substantially coplanar arrangement.

14. (Canceled)

15. (Canceled)

16. (Currently Amended) An electrostatic attraction mechanism for use in a surface processing device, the surface processing device including a processing chamber in which prescribed processing is carried out on a surface of a plate-

shaped object inside the processing chamber, the electrostatic attraction mechanism comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block,

wherein a first of the pair of attraction terminals is larger in size than a second of the pair of attraction terminals, and

a power source for applying a voltage to each of the attraction terminals to electrostatically attract a plate-shaped object to the dielectric block by inducing static electricity on the attraction surface,

wherein the voltage applied to each of the terminals can be individually adjusted in order to control a surface potential of the plate shaped object.

17. (Previously Presented) The electrostatic attraction mechanism of claim 16, wherein a plurality of pairs of attraction terminals are mounted inside the dielectric block.

18. (Currently Amended) The electrostatic attraction mechanism of claim [[16]] 17, wherein the voltage applied to each of the plurality of pairs of terminals can be individually adjusted in order to control the surface potential of the plate shaped object.

19. (Previously Presented) The electrostatic attraction mechanism of claim 16, wherein the pair of attraction terminals are arranged inside the dielectric block in a substantially coplanar arrangement.

20. (Canceled)

21. (Canceled)

22. (Previously Presented) The method of claim 7, wherein the pair of attraction terminals are arranged inside the dielectric block in a substantially coplanar arrangement.

23. (Previously Presented) The method of claim 7, wherein a first of the pair of attraction terminals is larger in size than a second of the pair of attraction terminals.

24. (Previously Presented) The method of claim 22, wherein a first of the pair of attraction terminals is larger in size than a second of the pair of attraction terminals.

25. (Canceled)

26. (Currently Amended) The electrostatic attraction mechanism of Claim [[25]] 30, wherein said control part has a recording part and a correspondence table comprising data on a relationship between the applied voltages and the surface potential, the correspondence table being obtained by measuring in advance the surface potential of the plate-shaped object while respectively changing the voltages applied to the attraction terminals and recording the respective voltages and surface potential in the recording part, and the control part controls said power source with a pattern of applied voltages selected in accordance with the correspondence table.

27. (Previously Presented) The electrostatic attraction mechanism of Claim 26, further comprising a recording part and a correspondence table comprising data on a relationship between the applied voltages and the surface potential, the correspondence table being obtained by measuring in advance the surface potential of the plate-shaped object while respectively changing the voltages applied to the attraction terminals and recording the respective voltages and surface potential in the recording part, and the adjusting means controls said applying means with a pattern of applied voltages selected in accordance with the correspondence table.

28. (New) An electrostatic attraction mechanism, comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block,

and

a power source for applying a voltage to each of the attraction terminals to electrostatically attract a plate-shaped object to the dielectric block by inducing static electricity on the attraction surface,

wherein the voltage applied to each of the terminals can be individually adjusted in order to control a surface potential of the plate shaped object in order to suppress an injection of charged particles into the plate-shaped object.

29. (New) An electrostatic attraction mechanism, comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block,

means for applying a voltage to each of the attraction terminals to electrostatically attract a plate-shaped object to the dielectric block by inducing static electricity on the attraction surface, and

means for individually adjusting the voltage applied to each of the terminals in order to control a surface potential of the plate shaped object in order to suppress an injection of charged particles into the plate-shaped object.

30. (New) An electrostatic attraction mechanism for use in a surface processing device, the surface processing device including a processing chamber in which prescribed processing is carried out on a surface of a plate-shaped object inside the processing chamber, the electrostatic attraction mechanism comprising:

a dielectric block having an attraction surface,

a pair of attraction terminals which are mounted inside the dielectric block,

and

a power source for applying a voltage to each of the attraction terminals to electrostatically attract a plate-shaped object to the dielectric block by inducing static electricity on the attraction surface,

wherein the voltage applied to each of the terminals can be individually adjusted in order to control a surface potential of the plate shaped object in order to suppress an injection of charged particles into the plate-shaped object..